

**UNIVERSITÀ DEGLI STUDI DI PADOVA
SCIENCE FACULTY**

MATERIAL SCIENCE DEGREE

INFN – LABORATORI NAZIONALI DI LEGNARO

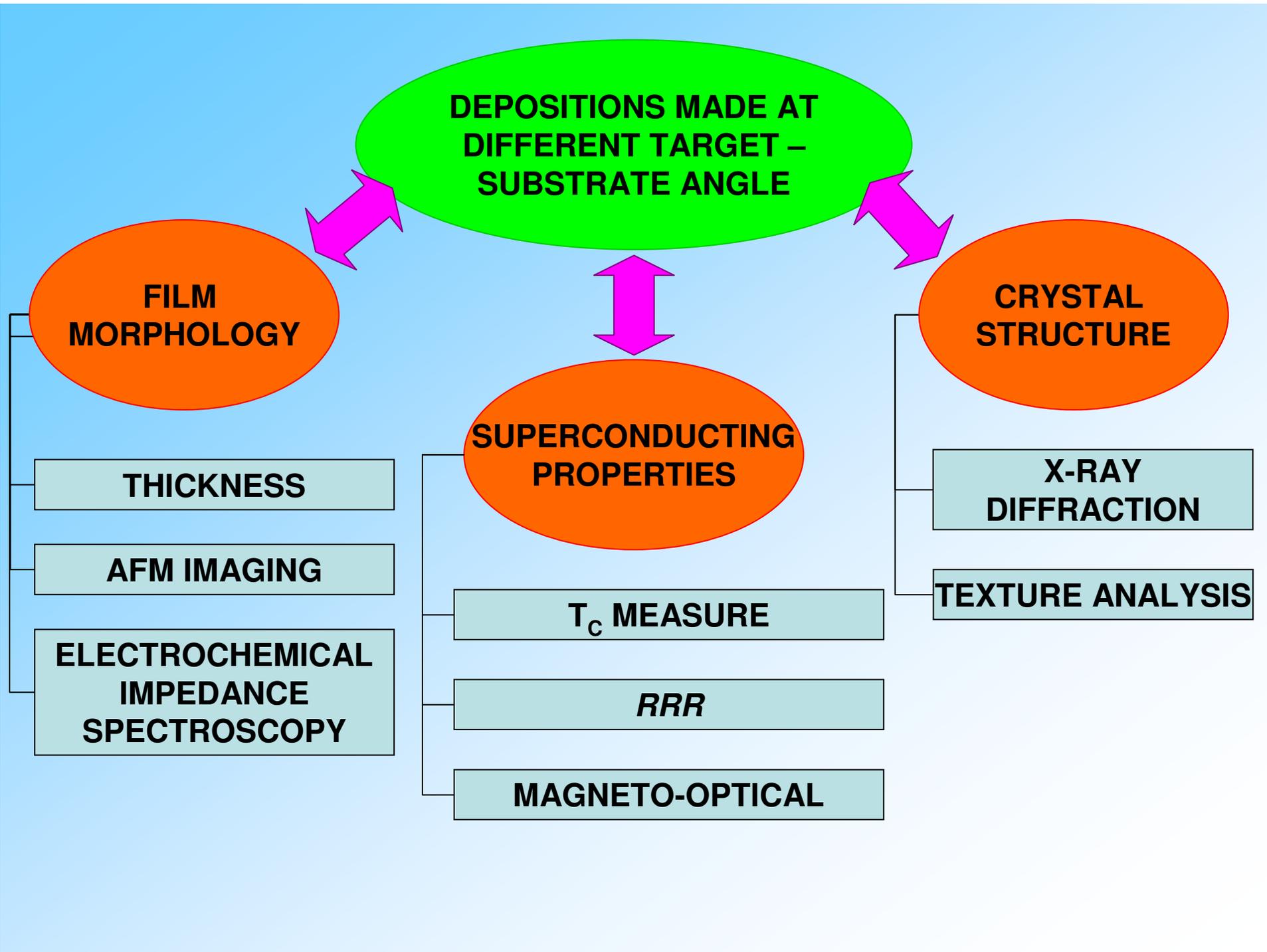
DIEGO TONINI

**MORPHOLOGY OF NIOBIUM FILMS SPUTTERED AT
DIFFERENT TARGET – SUBSTRATE ANGLE**

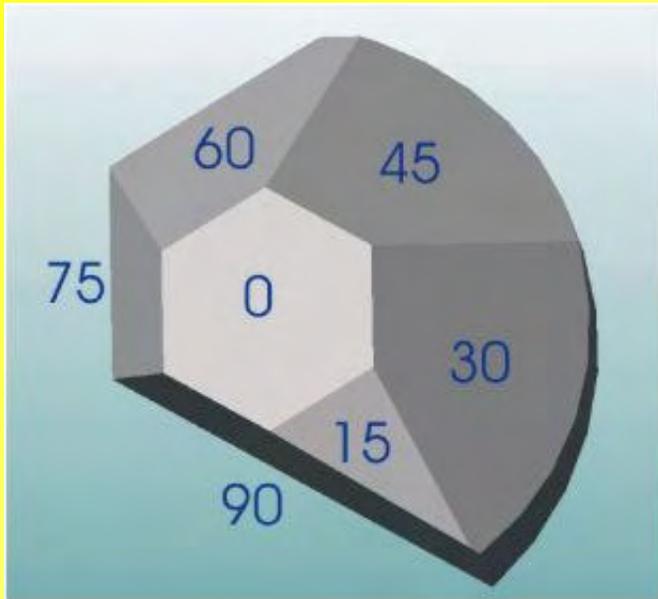


2 QUESTIONS...

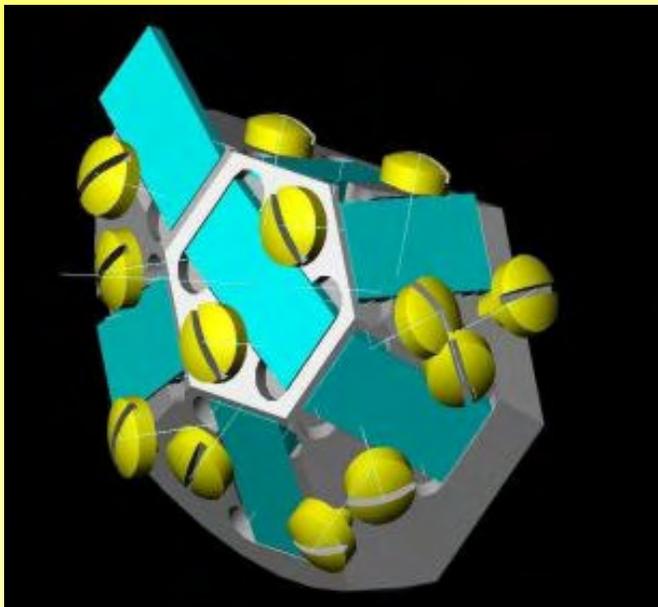
- ***What is the effect of target – substrate angle on the film properties?***
- ***How the film morphology varies changing target – substrate angle?***



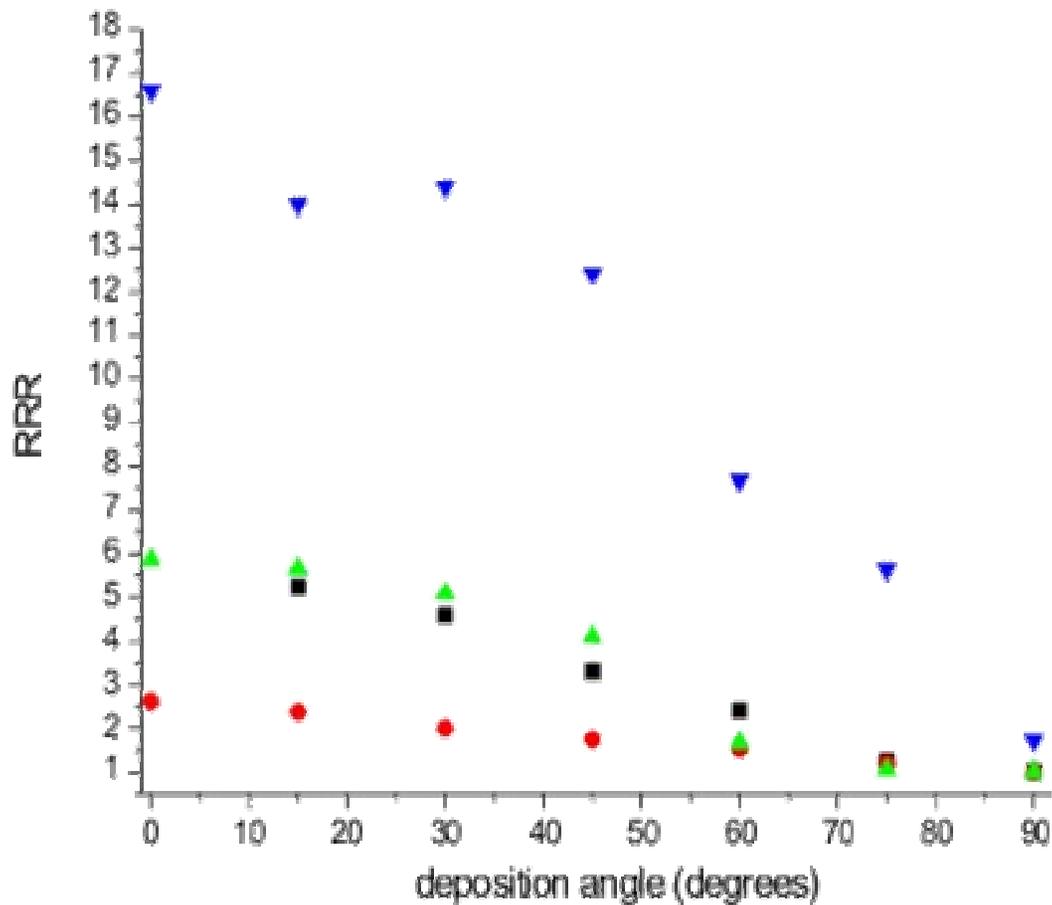
MULTI-ANGLE SAMPLE HOLDER



- **7 substrates coated in the same run**
- **Almost identical process conditions for each sample**

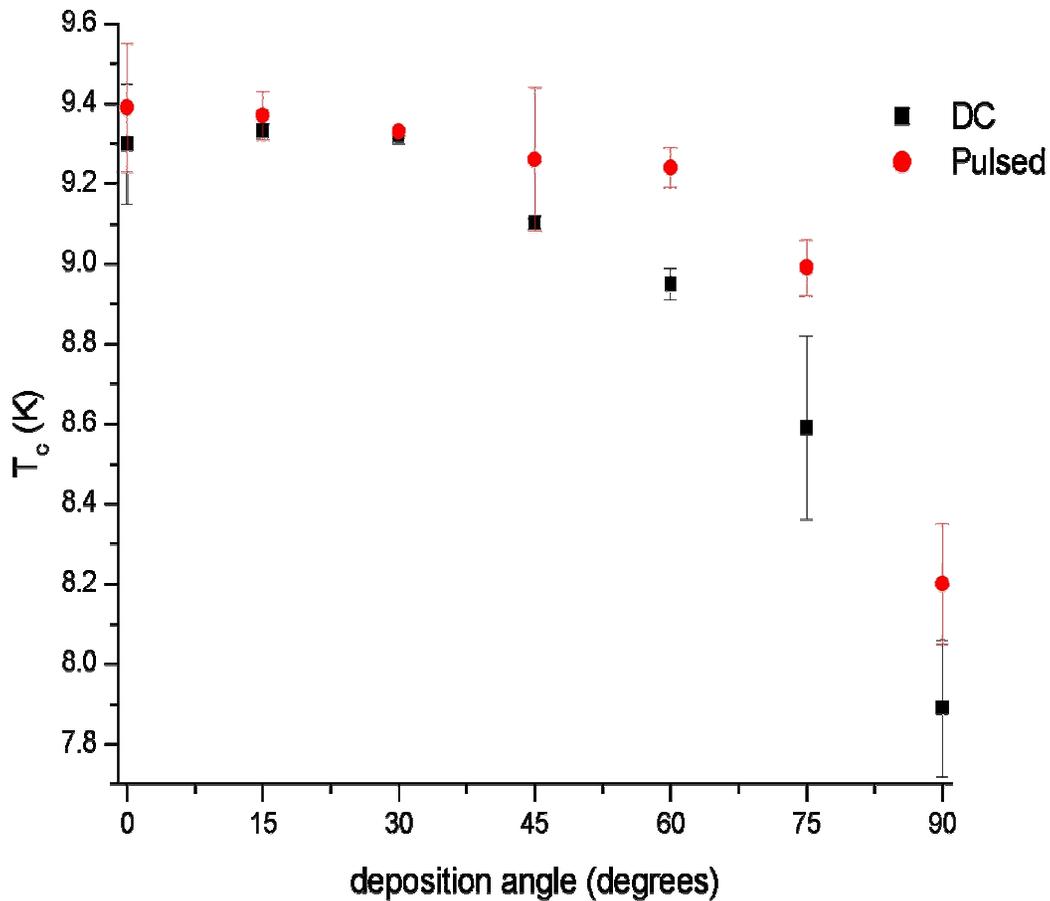


DC MAGNETRON SPUTTERING



- **LOWER T_C AND *RRR* INCREASING TARGET – SUBSTRATE ANGLE**

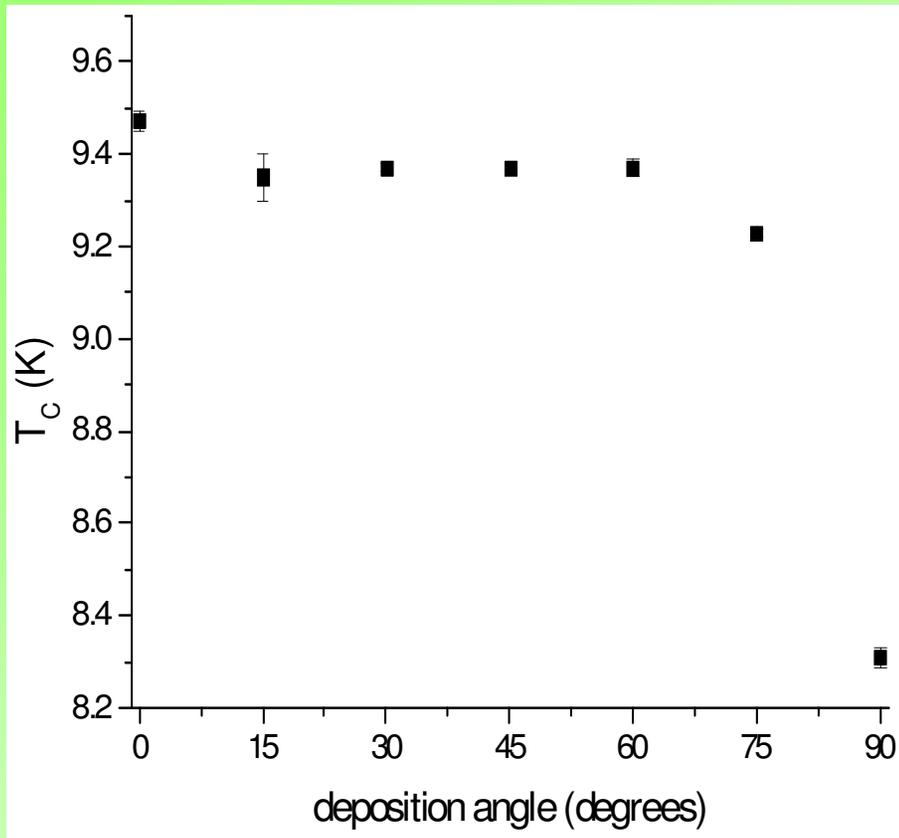
PULSED MAGNETRON SPUTTERING



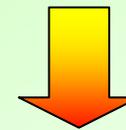
- **BETTER PROPERTIES FOR PULSED CURRENT DEPOSITION**

- **THERE IS STILL THE SAME ANGLE DEPENDENCE OF T_c AND *RRR***

DC MAGNETRON SPUTTERING WITH SUBSTRATE HEATING

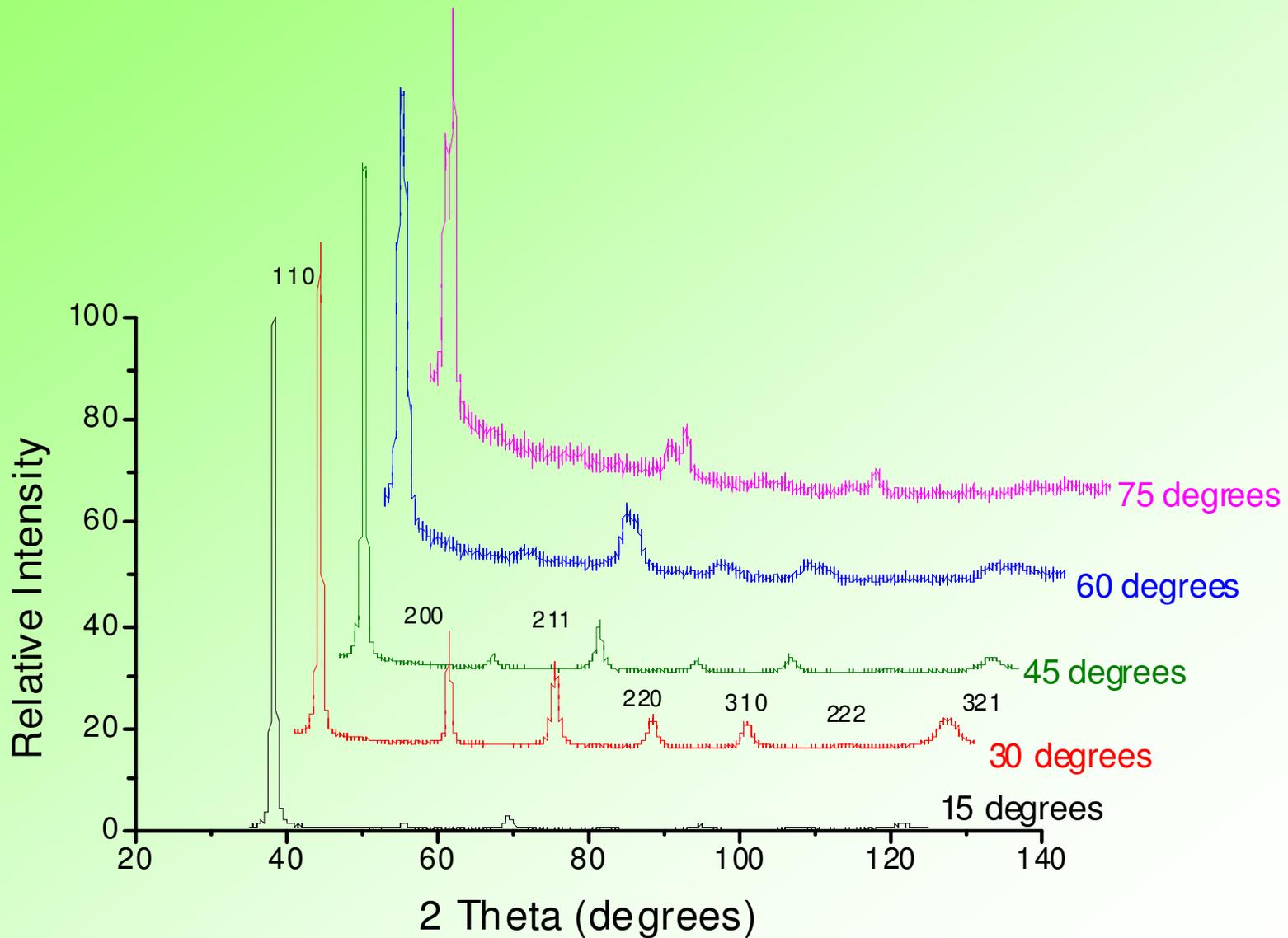


**Substrate temperature
kept at 600 °C during
process**



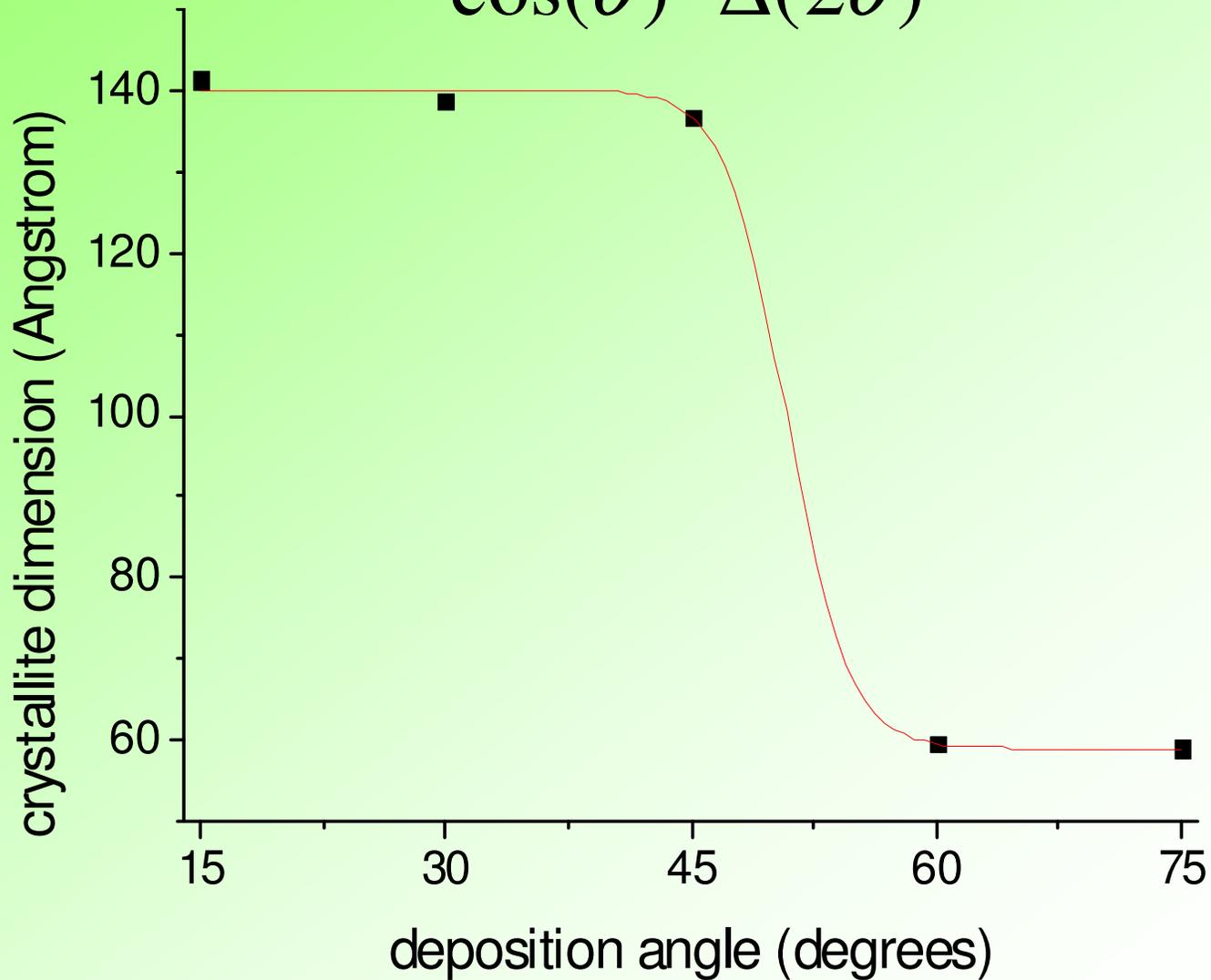
- 1. Better properties**
- 2. Less angle sensitivity**

XRD SPECTRA OF FILM DEPOSITED AT DIFFERENT TARGET – SUBSTRATE ANGLE



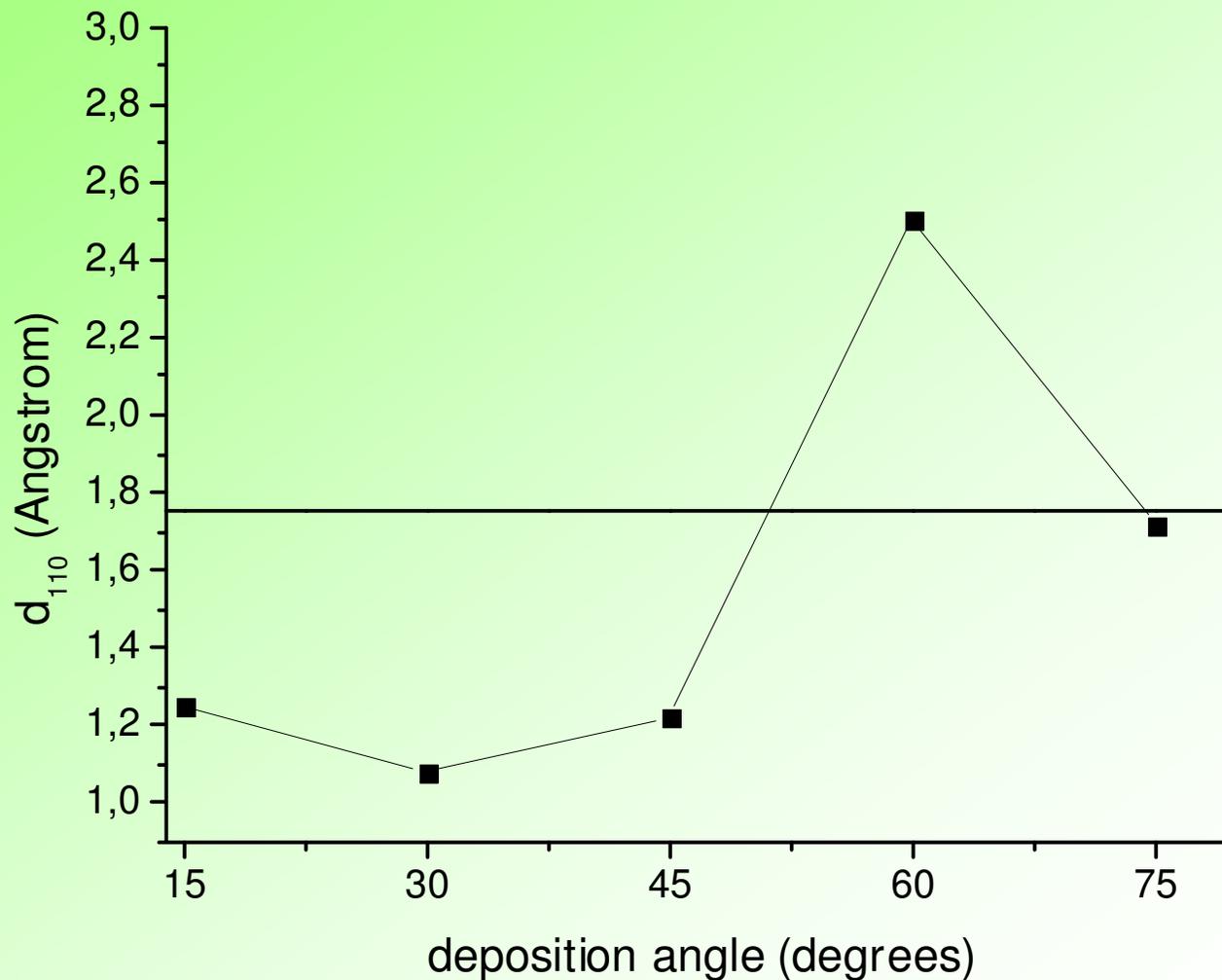
ESTIMATED GRAIN DIMENSION

$$D = \frac{0.9\lambda}{\cos(\theta) \cdot \Delta(2\theta)}$$

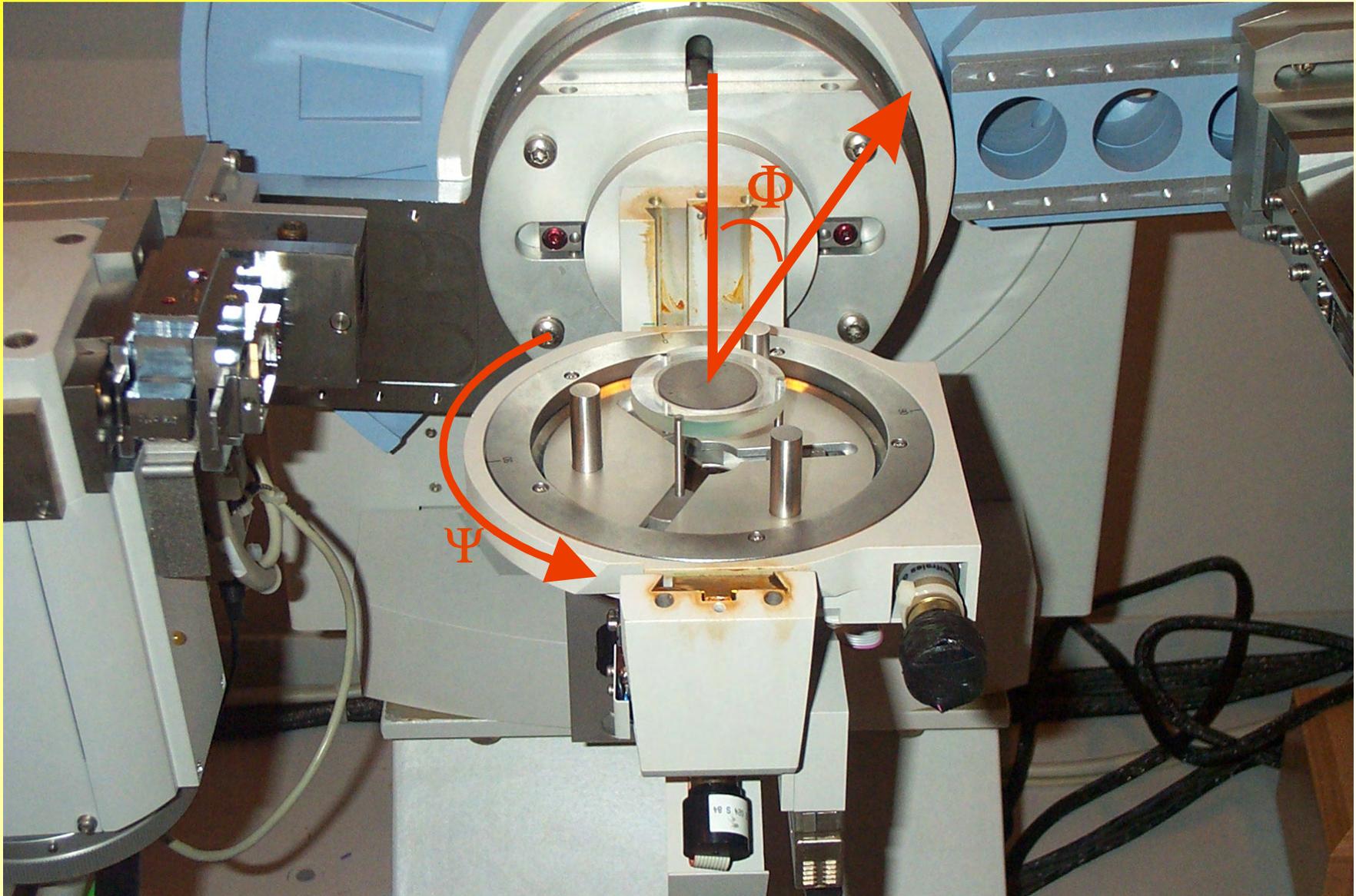


d_{110} OF CRYSTAL PLANES

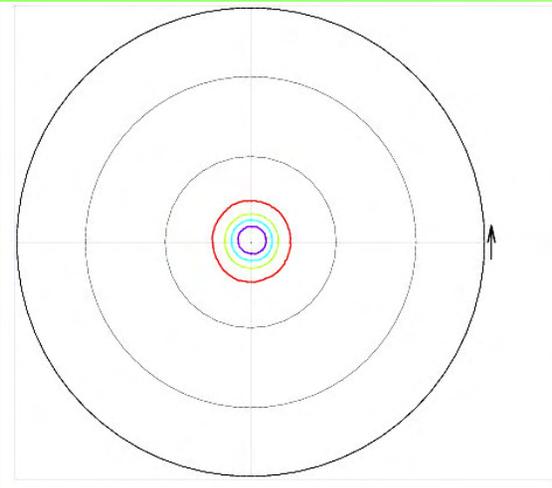
$$2d_{(hkl)} \sin \theta = n\lambda$$



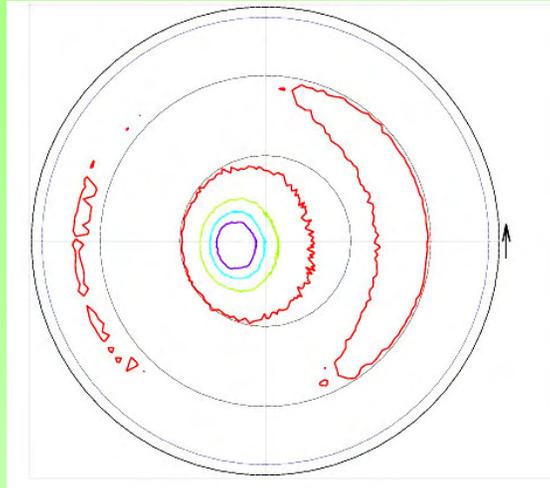
TEXTURE ANALYSIS



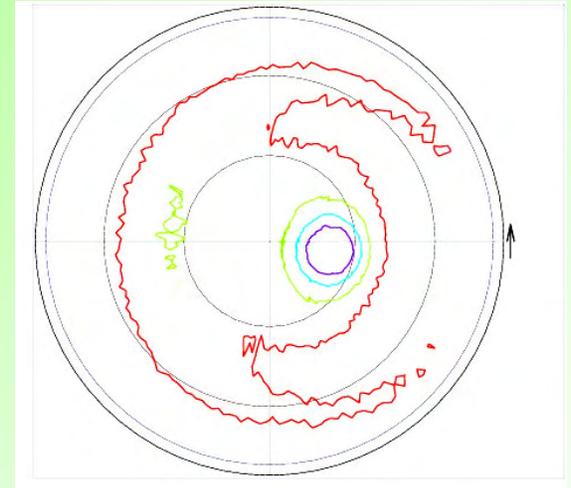
DC MAGNETRON SPUTTERING



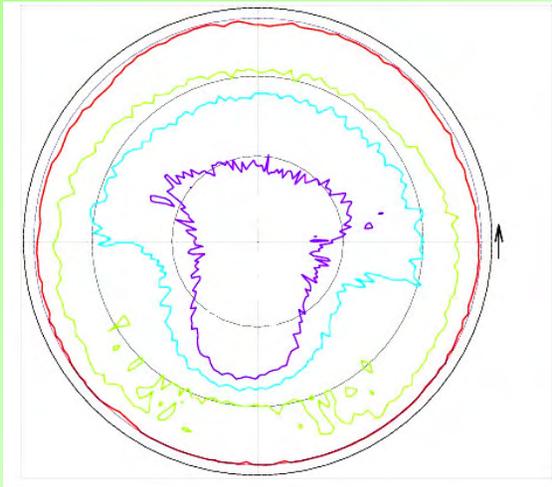
0 gradi



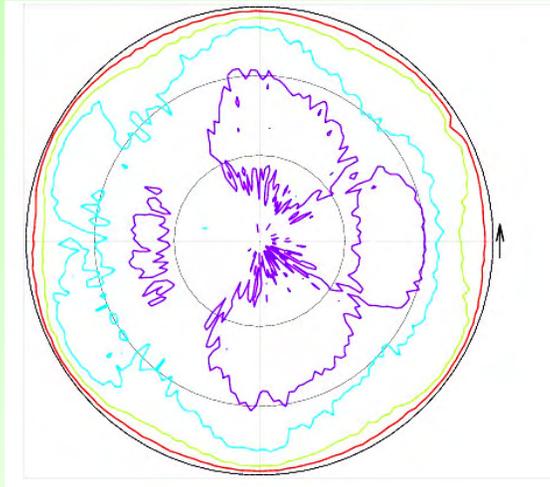
15 gradi



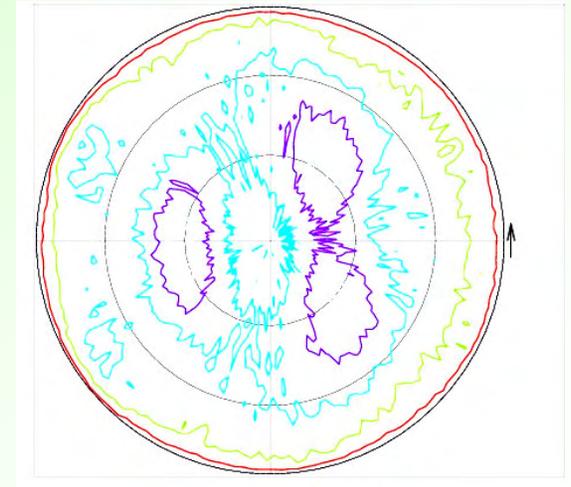
30 gradi



45 gradi

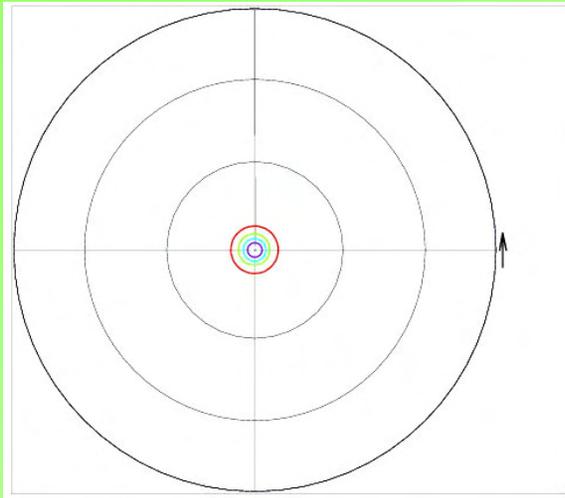


60 gradi

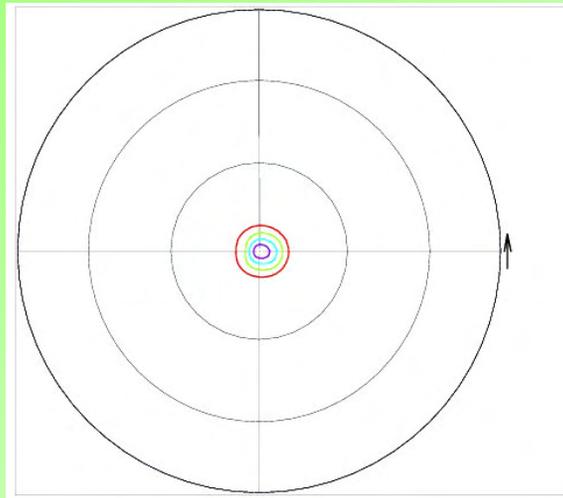


75 gradi

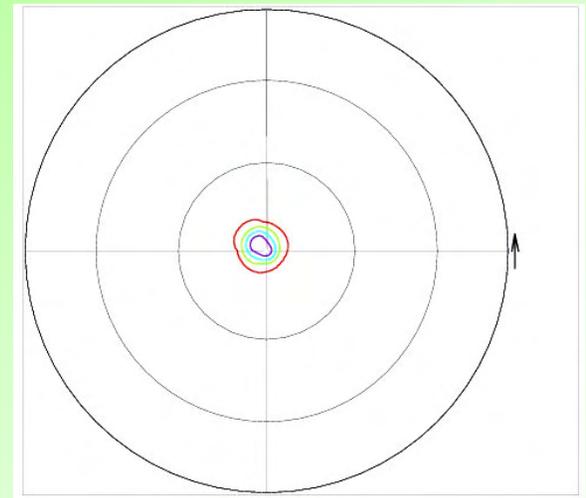
PULSED MAGNETRON SPUTTERING



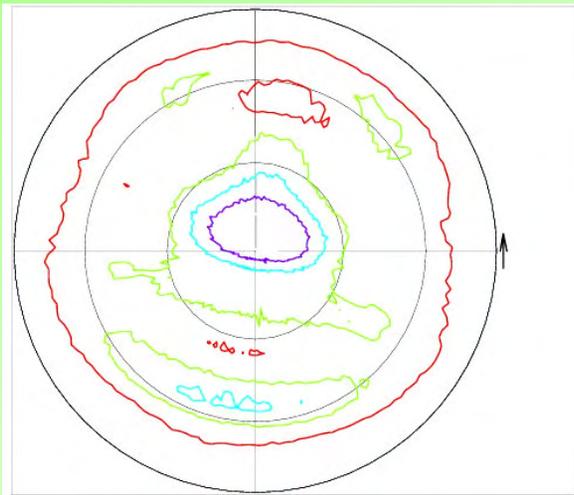
0 gradi



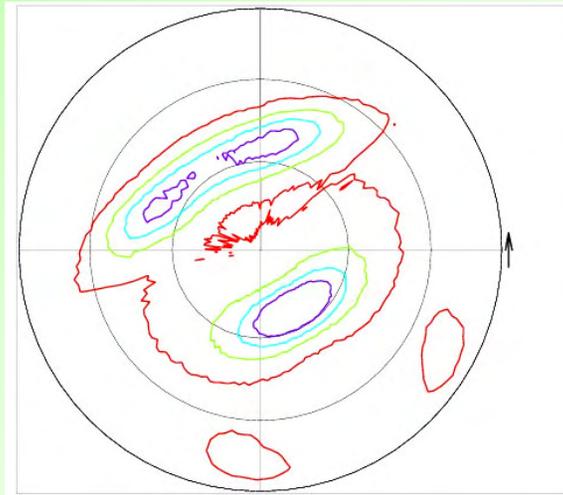
15 gradi



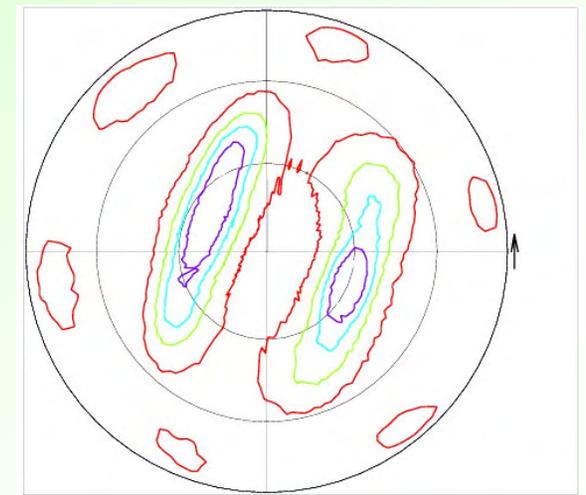
30 gradi



45 gradi



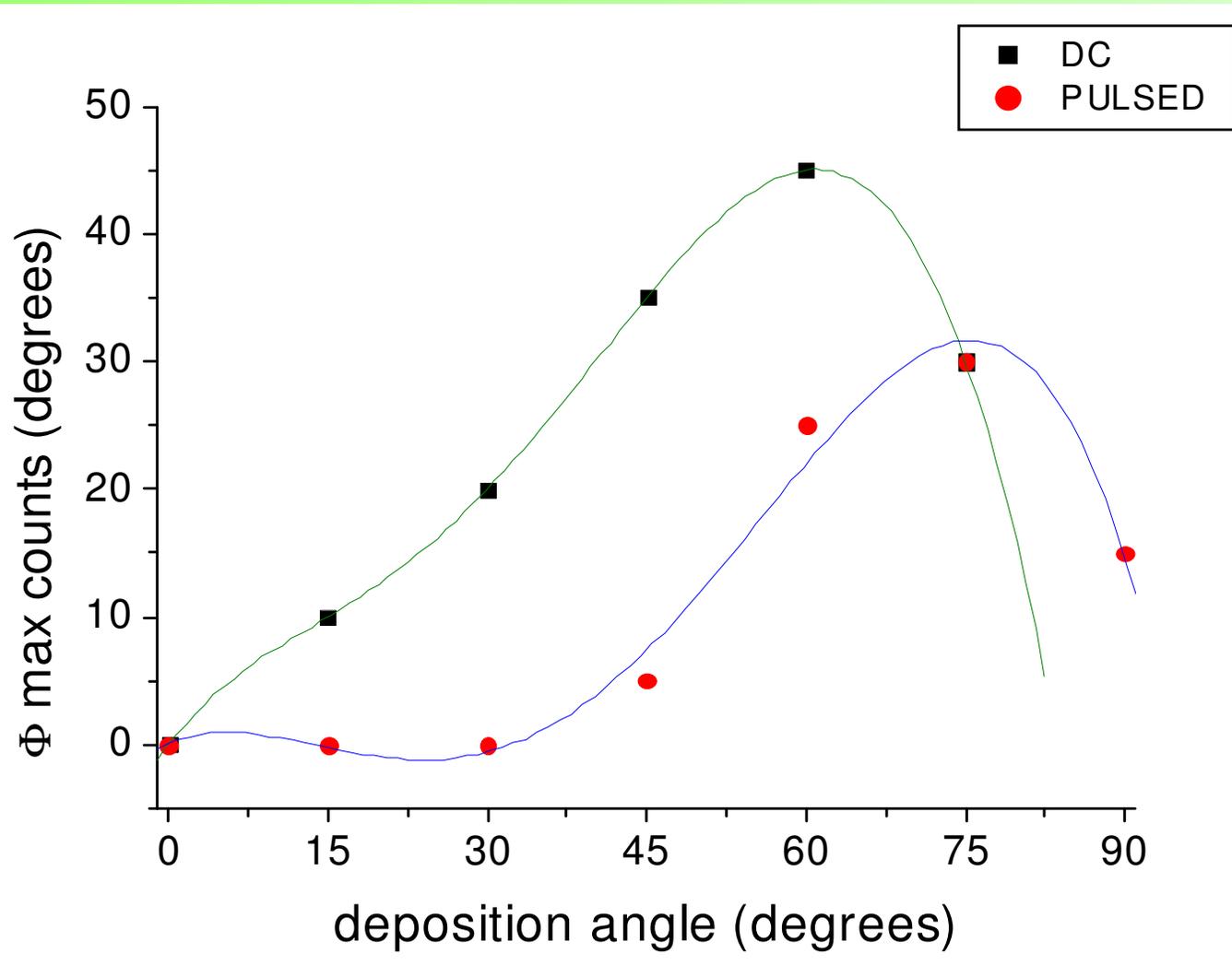
60 gradi



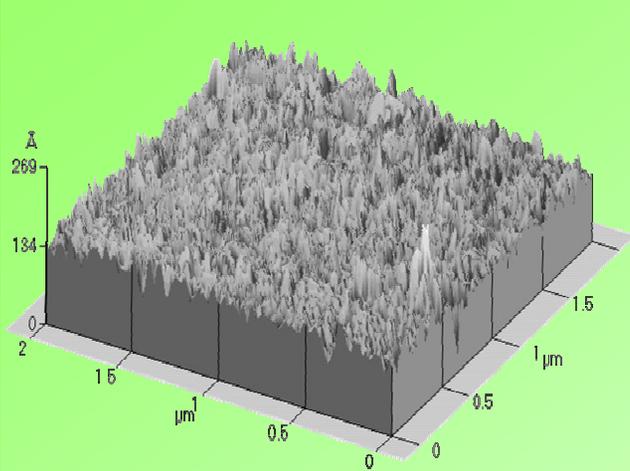
75 gradi

TEXTURE ANALYSIS

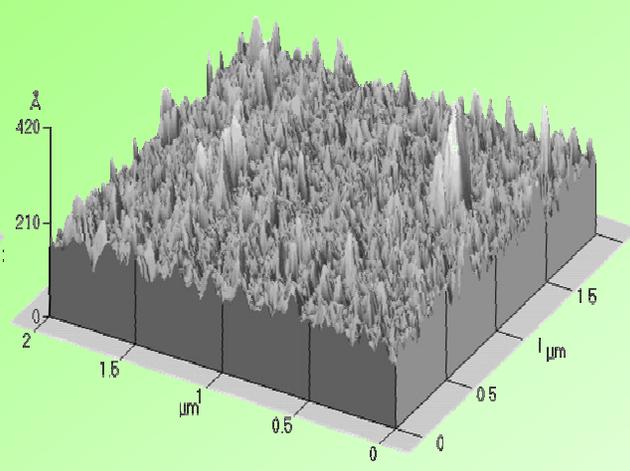
DC VS PULSED MAGNETRON SPUTTERING



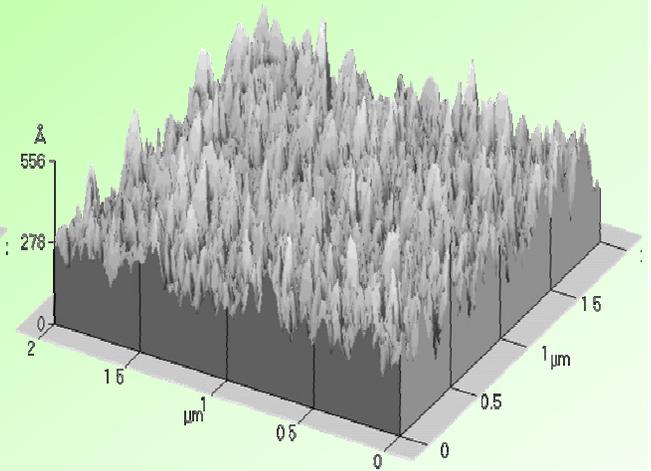
ATOMIC FORCE MICROSCOPY TOPOGRAPHIC IMAGES



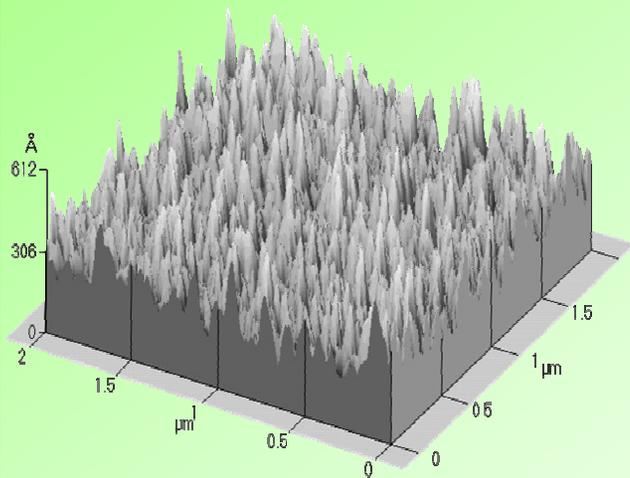
15 gradi



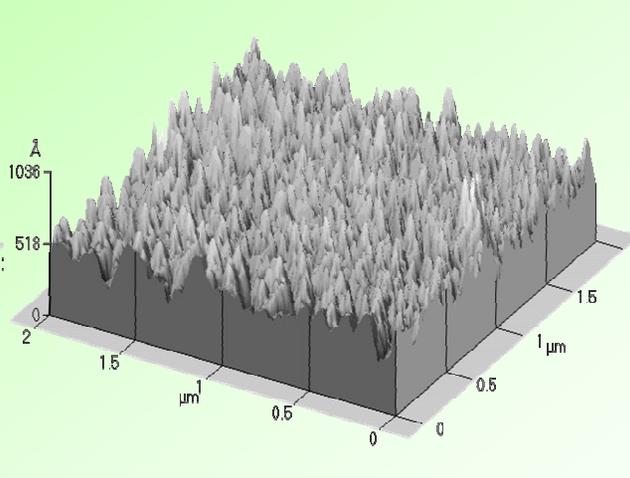
30 gradi



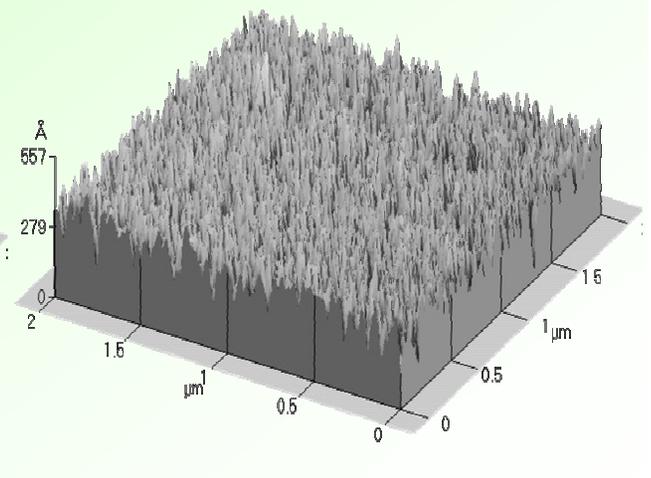
45 gradi



60 gradi

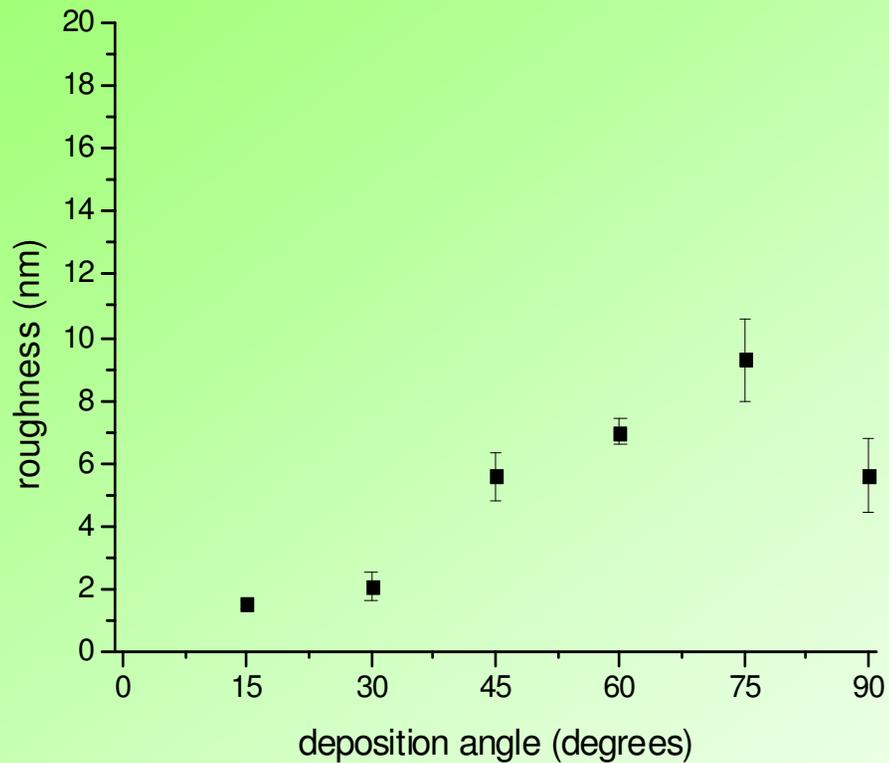


75 gradi

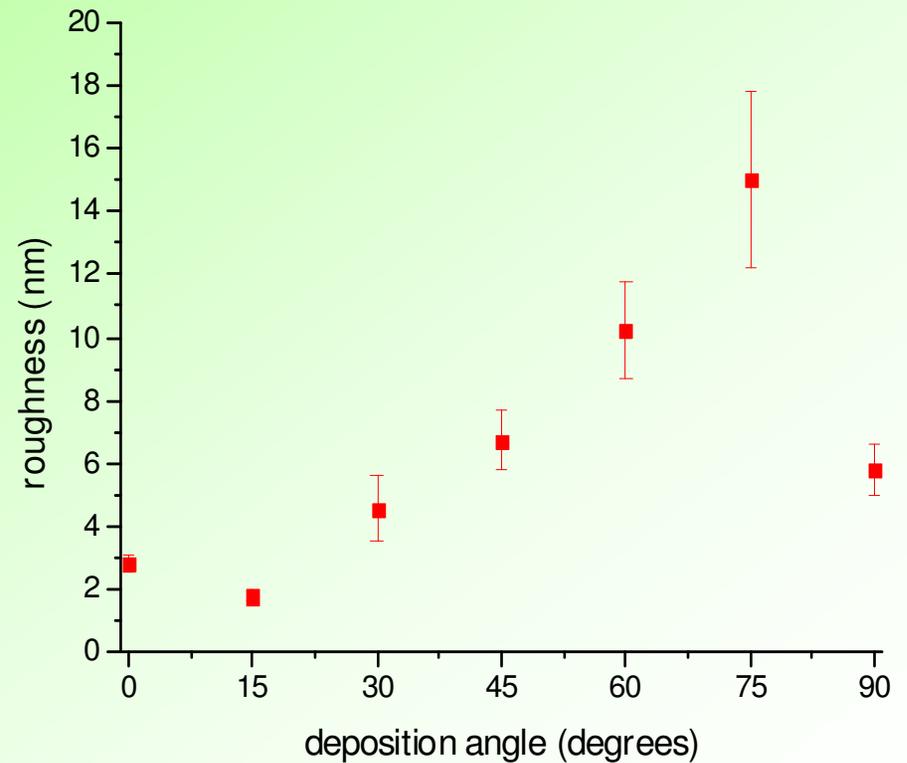


90 gradi

ATOMIC FORCE MICROSCOPY DC MAGNETRON SPUTTERING

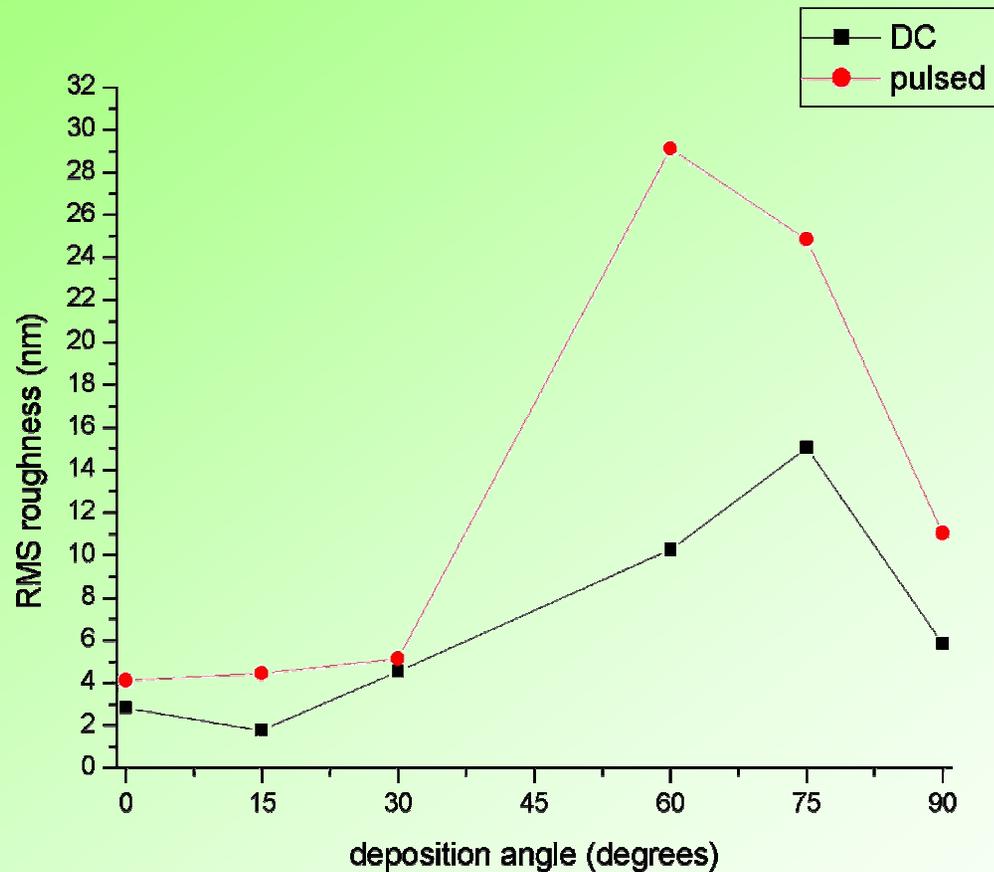


Variable thickness



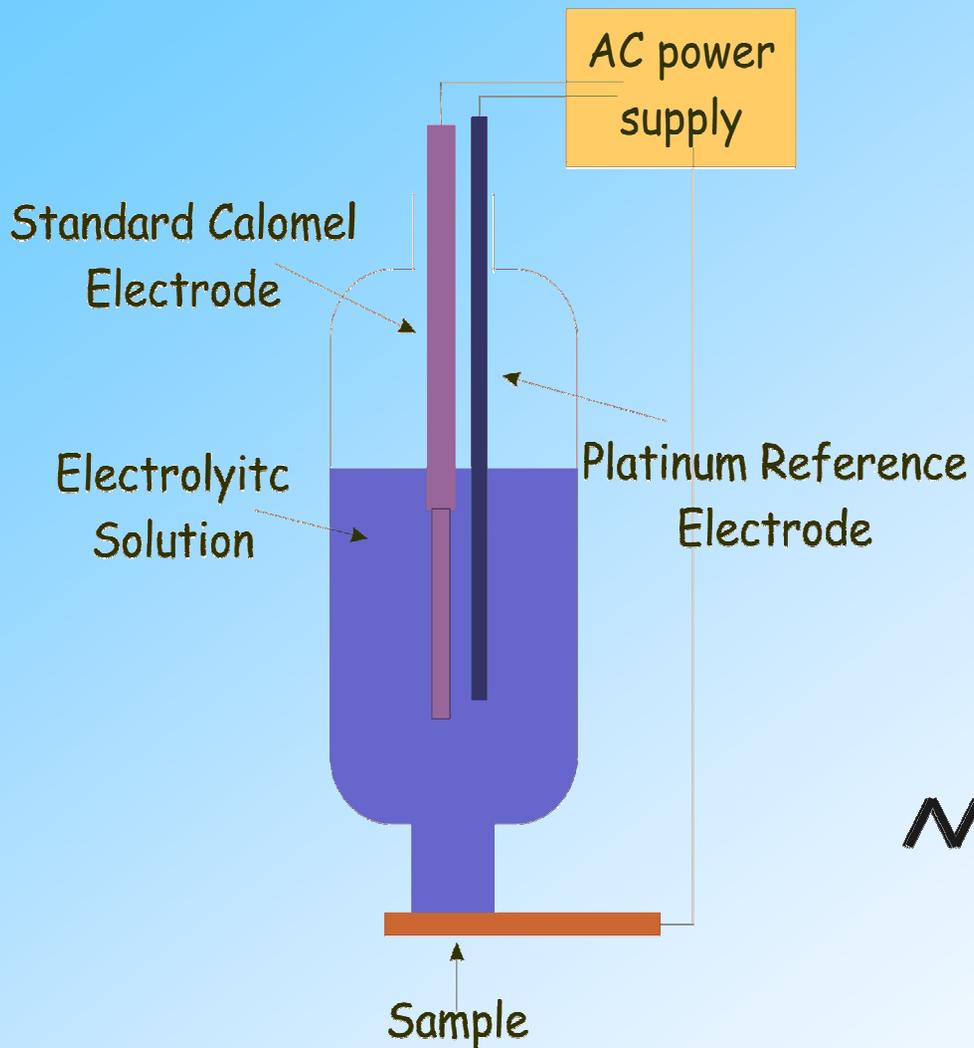
Uniform thickness

ATOMIC FORCE MICROSCOPY PULSED MAGNETRON SPUTTERING



***I campioni depositati in corrente pulsata sono
sistematicamente più rugosi***

ELECTROCHEMICAL IMPEDANCE SPECTROSCOPY

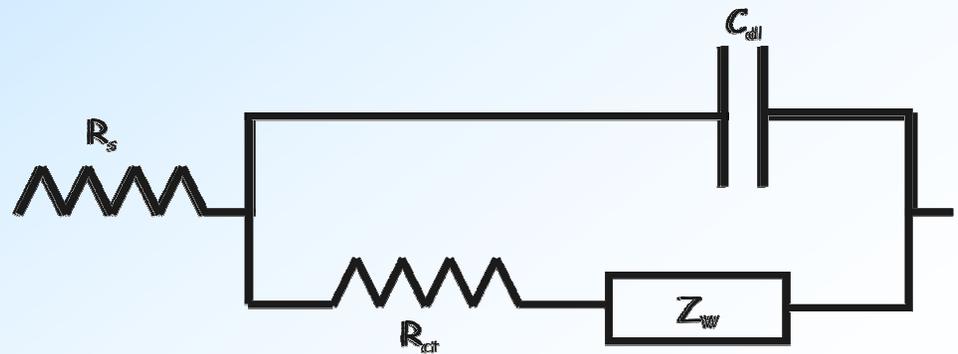


$$V(t) = V_0 \cos(\omega t)$$

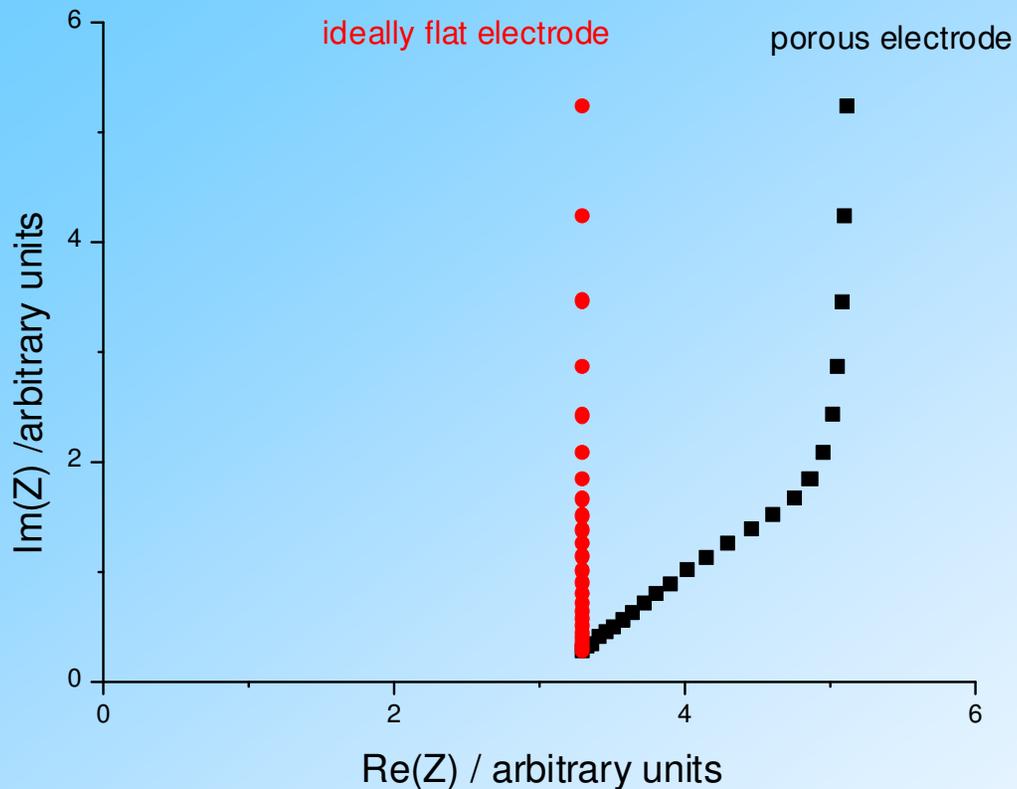
$$I(t) = I_0 \cos(\omega t - \varphi)$$

$$Z = \frac{V(t)}{I(t)} = Z_0 \frac{\cos(\omega t)}{\cos(\omega t - \varphi)}$$

$$Z = Z_0 e^{j\varphi}$$



ELECTROCHEMICAL IMPEDANCE SPECTROSCOPY NYQUIST PLOT



FLAT ELECTRODE:

Real part of impedance represents R_s at any frequency

Imaginary part does not vary with frequency

NYQUIST PLOT IS A VERTICAL LINE

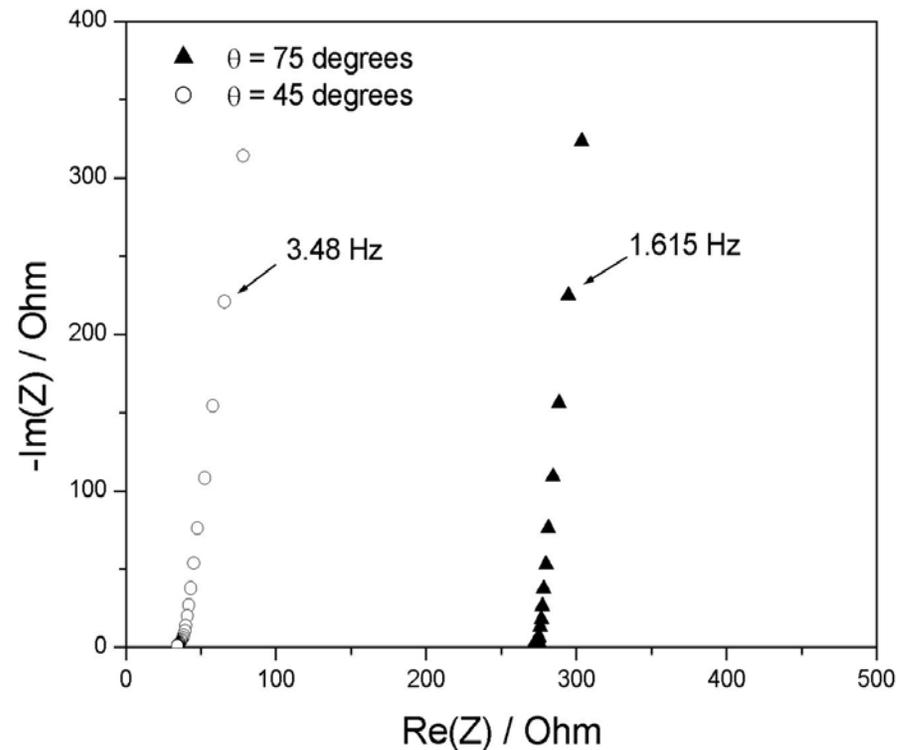
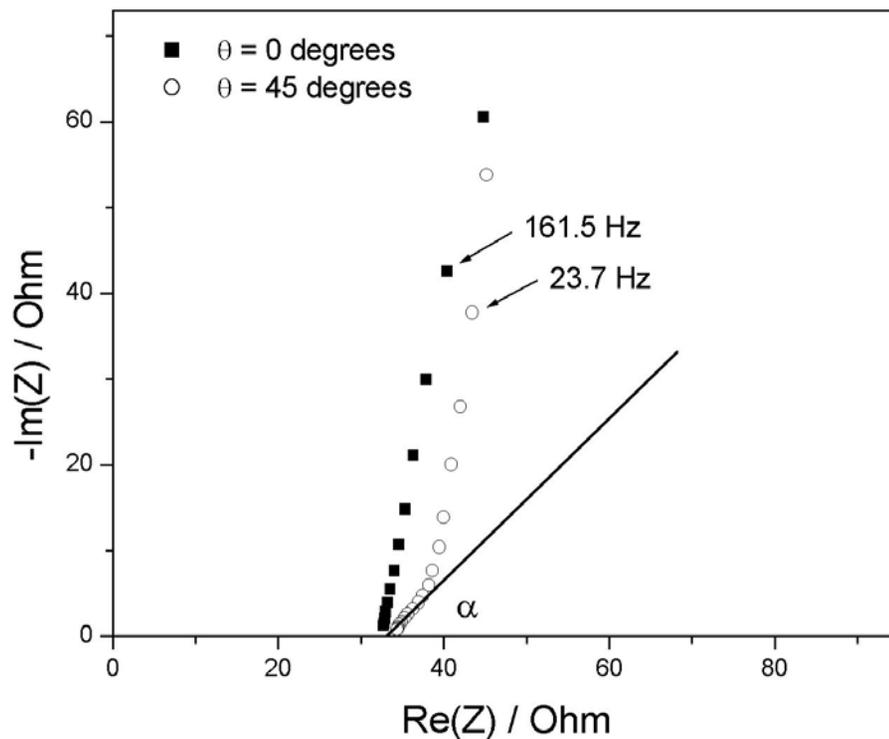
POROUS/ROUGH ELECTRODE:

The apparent capacity C_{dl} depends on frequency because the penetration length of electric field inside the pores raises when decreasing frequency.

NYQUIST PLOT IS A 45° INCLINED LINE

ELECTROCHEMICAL IMPEDANCE SPECTROSCOPY DC MAGNETRON SPUTTERING

VARIABLE FILM THICKNESS



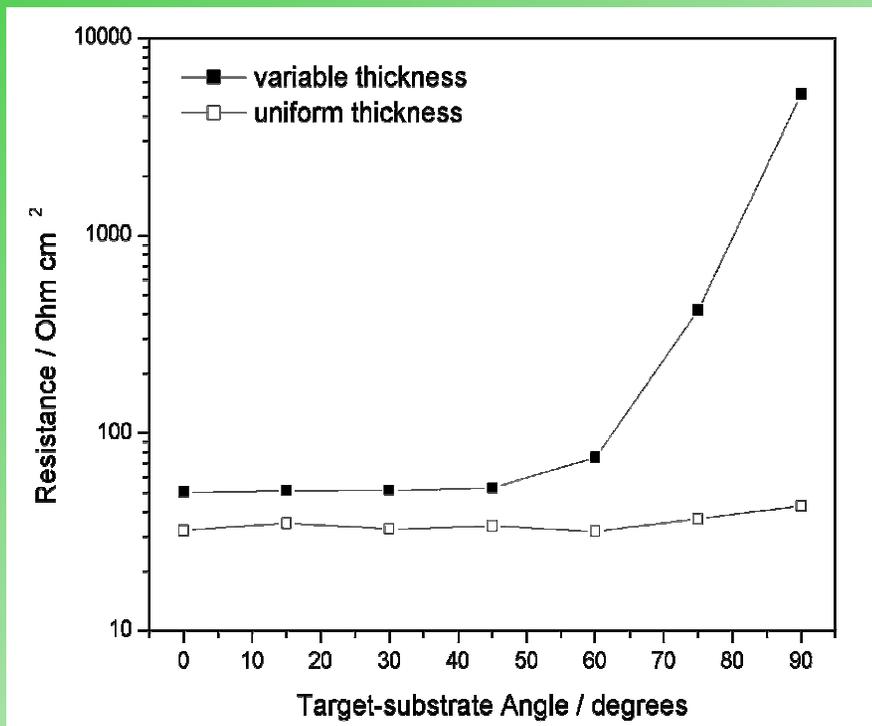
Up to 45° there is porous electrode behaviour

Film deposited at higher angles are less thick so resistance is greater

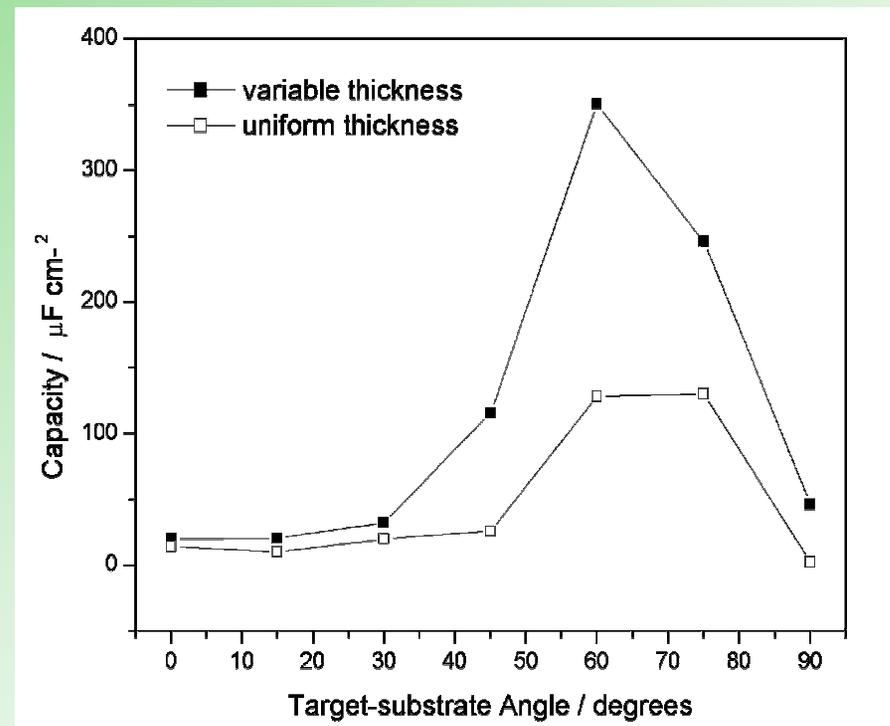
ELECTROCHEMICAL IMPEDANCE SPECTROSCOPY

DC MAGNETRON SPUTTERING

COMPARISON BETWEEN FILM WITH DIFFERENT THICKNESS AND FILM WITH CONSTANT THICKNESS



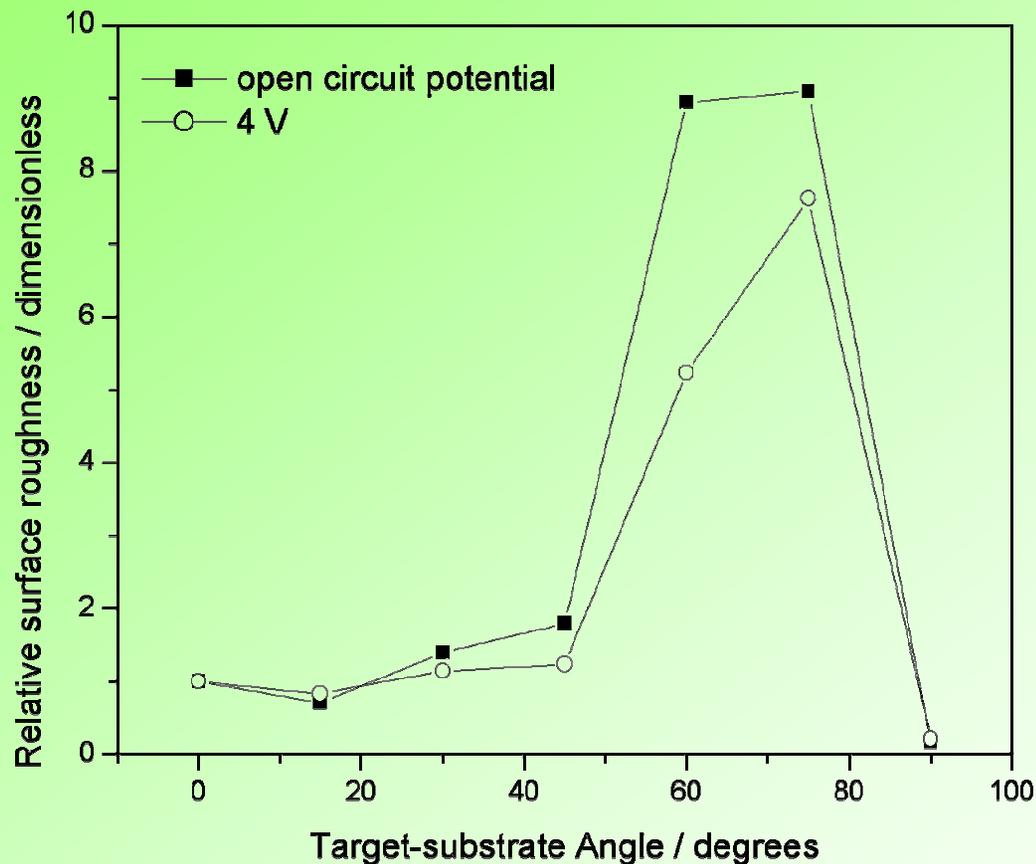
Films with the same thickness have the same resistance



There is a maximum in capacity at 60° target – substrate angle

ELECTROCHEMICAL IMPEDANCE SPECTROSCOPY DC MAGNETRON SPUTTERING

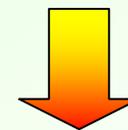
***Films with the same thickness –
measures in passivation condition***



***Imposed potential to create a
passivation layer on the film***

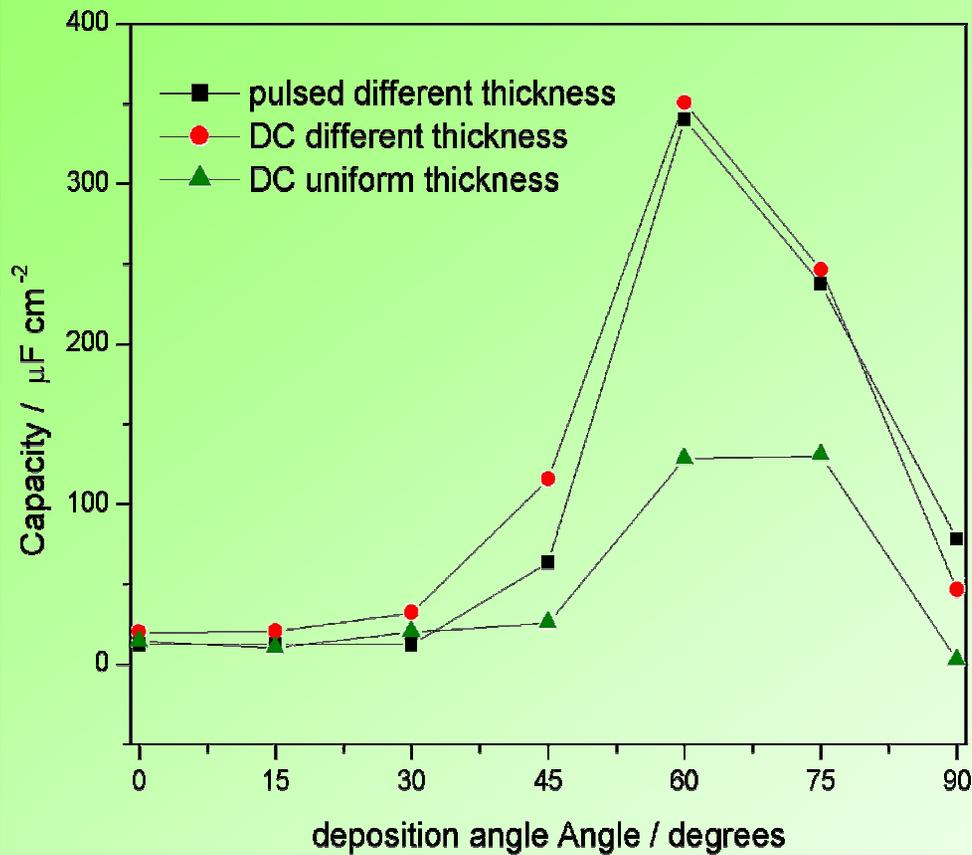
***Oxide thickness depends only
on applied potential***

***Oxide growth follows niobium
film morphology***

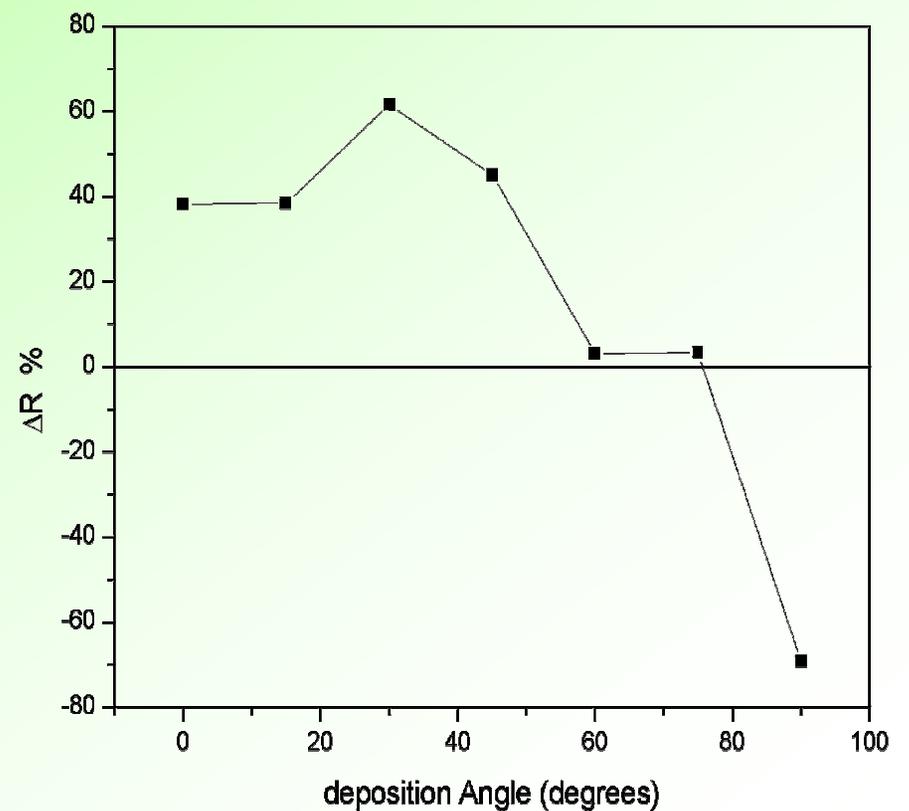


***Capacity shows the same
angle dependence of non
oxidized films***

ELECTROCHEMICAL IMPEDANCE SPECTROSCOPY PULSED MAGNETRON SPUTTERING

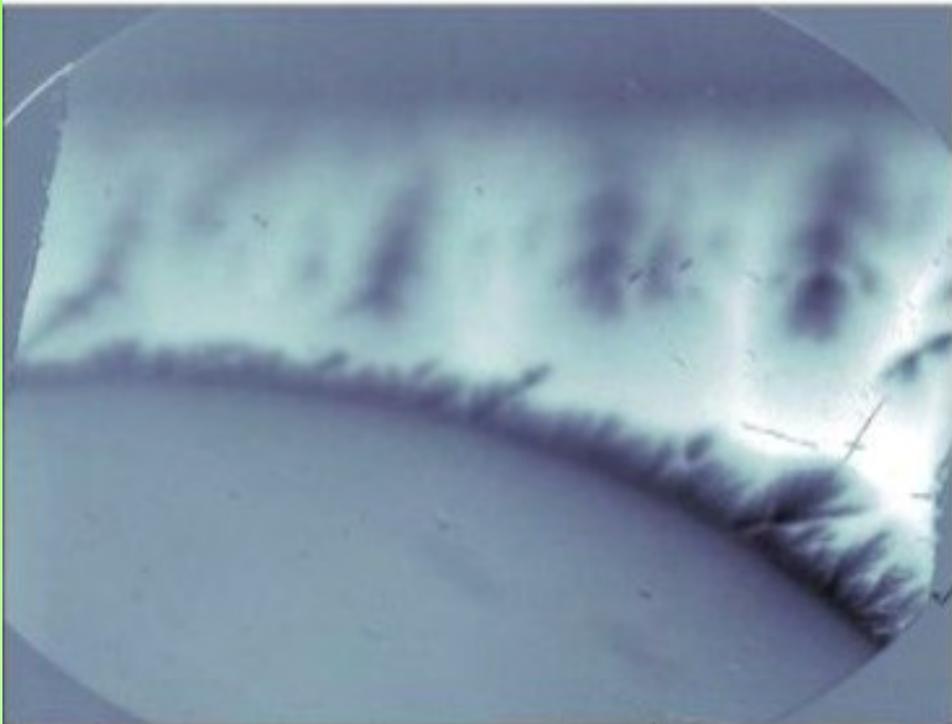


$$\Delta R = \frac{C_{ac}^{cont} - C_{ac}^{pulsed}}{C_{ac}^{pulsed}} \times 100$$



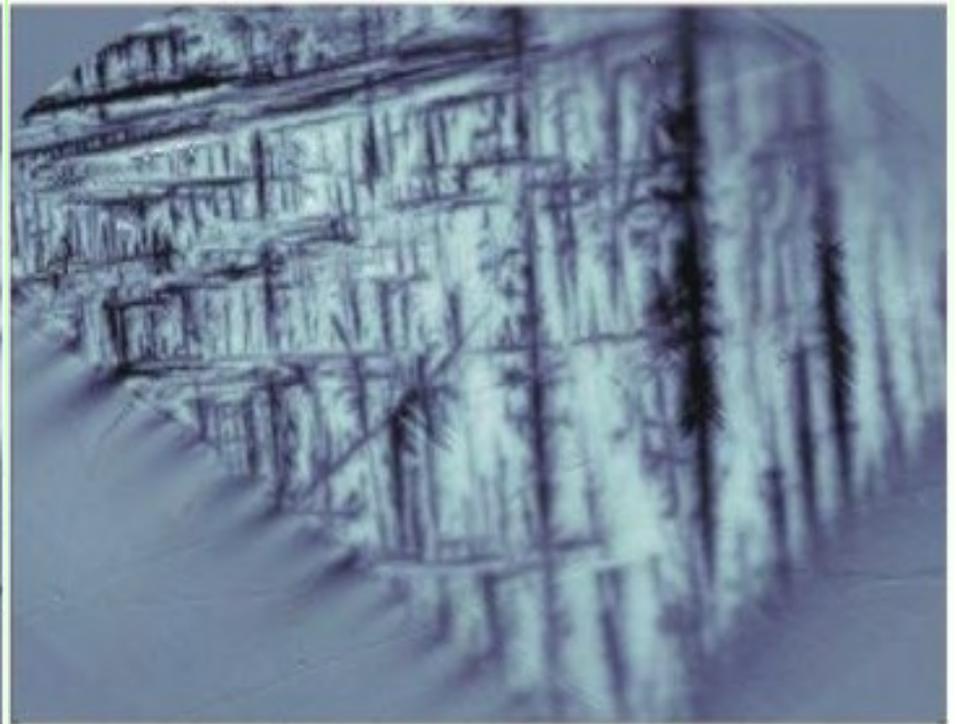
MAGNETO-OPTICAL ANALYSIS

OFHC copper substrate (not electropolished)



Target – substrate angle: 0°

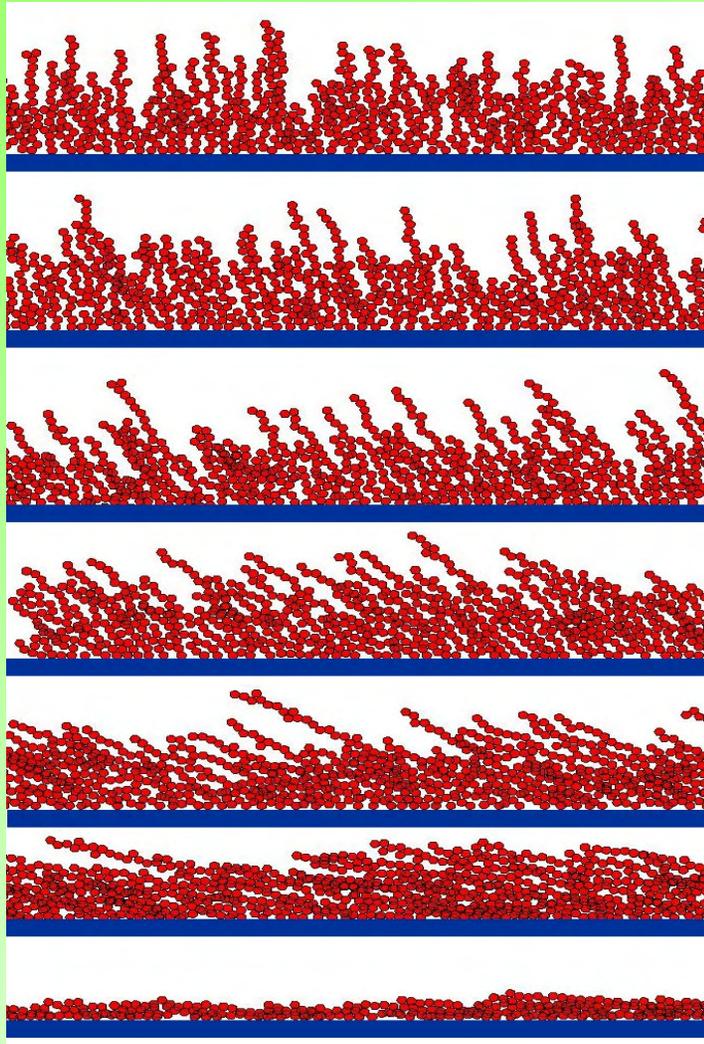
Good connectivity respect to vortex penetration



Target – substrate angle: 45°

Vortex penetrate along substrate discontinuity

SIMULATION OF THIN FILM GROWTH



0°

15°

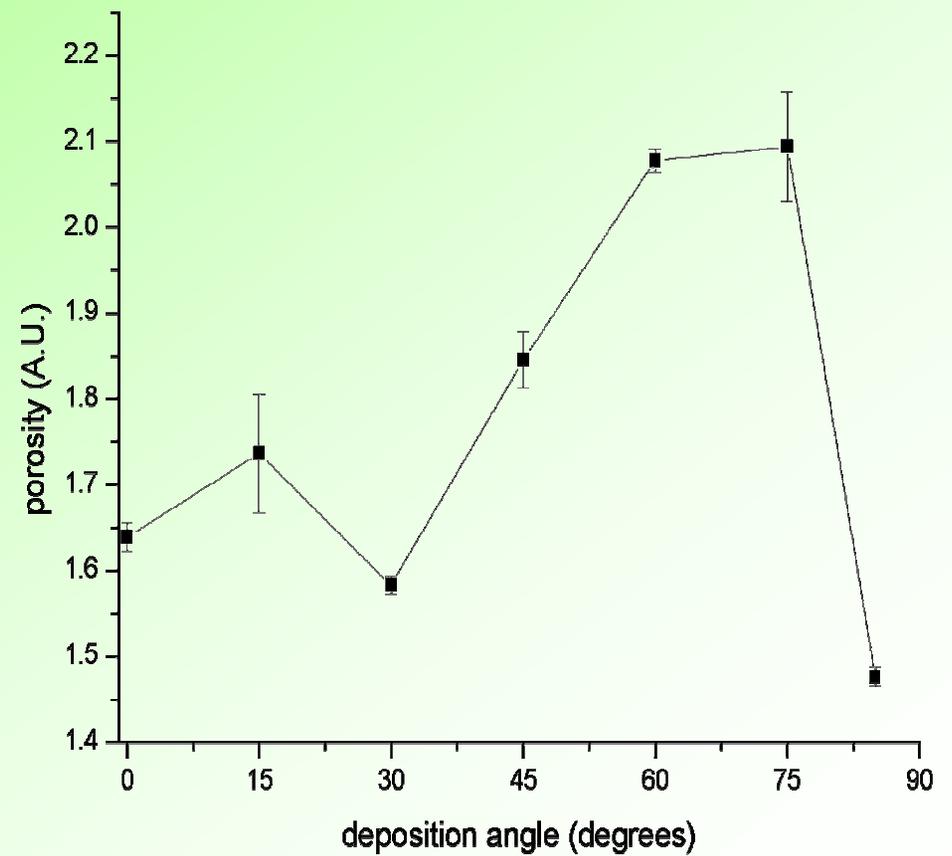
30°

45°

60°

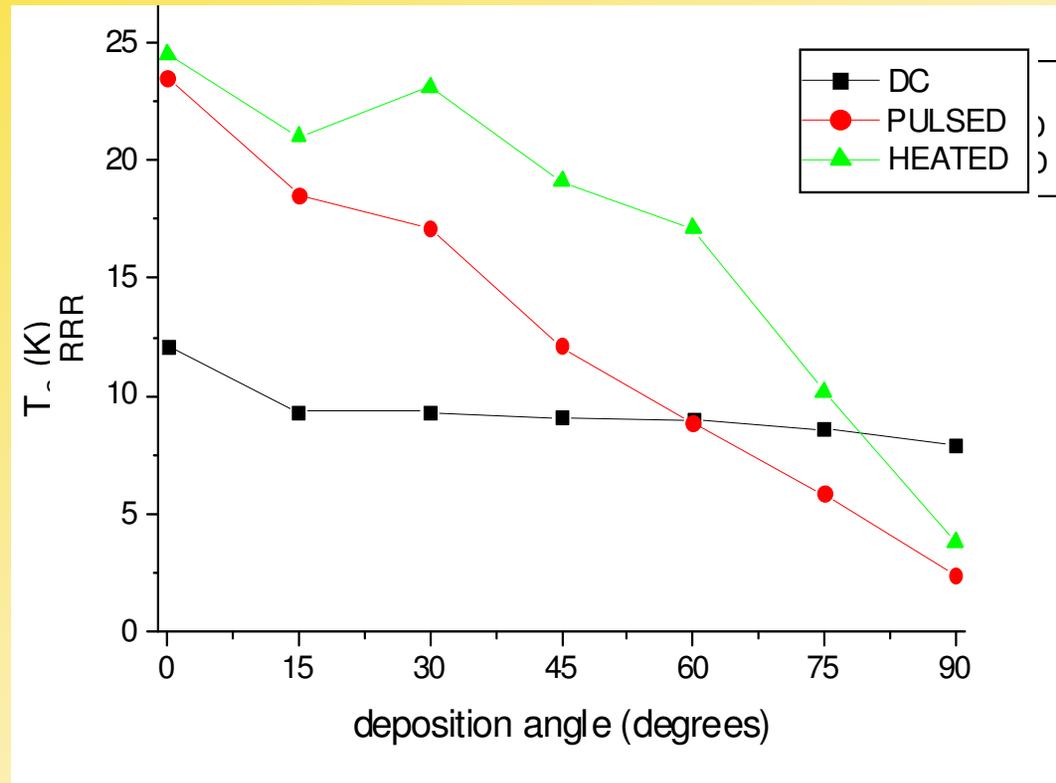
75°

85°



CONCLUSIONS

s.c. and transport properties



Properties depend on target – substrate angle

Pulsed magnetron sputtering and heating of the substrate reduce the angle dependence

CONCLUSIONS

Crystal structure

Films deposited at higher angles tend towards amorphization

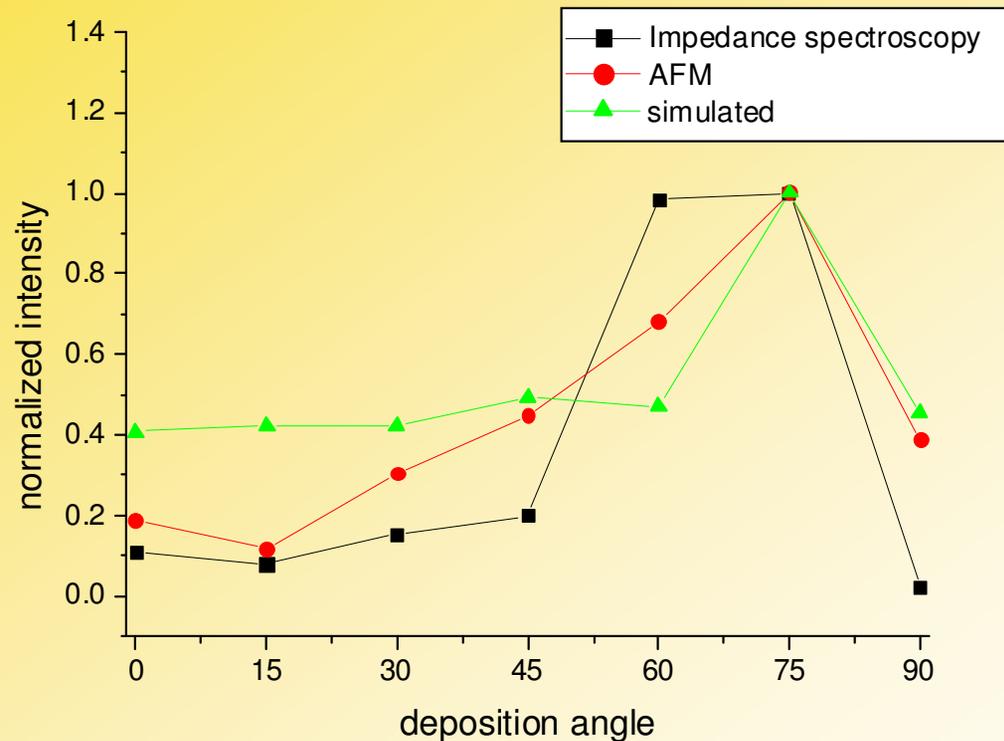
Lattice parameter has a maximum at 60° target – substrate angle

(110) crystal planes of the growing film orient along niobium atoms arrival direction

This effect is reduced using pulsed magnetron deposition

CONCLUSIONS

morphology



There is a maximum in roughness between 60° and 75° target – substrate angle

This is not a thickness effect but is due to deposition dynamics

Fine.